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1. A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands over a glass substrate;
subjecting said semiconductor islands to an ion doping;
directing a pulsed excimer laser beam having a cross section elongated in one direction to said glass substrate;
moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed excimer laser beam, thereby irradiating said semiconductor islands with said pulsed excimer laser beam.

2. A method according to claim 1 wherein an energy density of said pulsed excimer laser beam is not higher than 300 mJ/cm².

3. A method according to claim 1 wherein an impurity selected from the group consisting of phosphorus and boron is selectively introduced into said plurality of semiconductor islands by said ion doping.

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4. A method according to claim 1 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed excimer laser beam.

5. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a glass substrate;
crystallizing said semiconductor film;
patterning the crystallized semiconductor film into a plurality of semiconductor islands;
subjecting said semiconductor islands to an ion doping;
directing a pulsed excimer laser beam having a cross section elongated in one direction to said glass substrate;
moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed excimer laser beam, thereby irradiating said semiconductor islands with said pulsed excimer laser beam.

6. A method according to claim 5 wherein an energy density of said pulsed excimer laser beam is not higher than 300 mJ/cm^2 .

7. A method according to claim 5 wherein an impurity selected from the group consisting of phosphorus and boron is selectively introduced into said plurality of semiconductor islands by said ion doping.

8. A method according to claim 5 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed excimer laser beam

9. A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of first semiconductor islands and a plurality of second semiconductor islands over a glass substrate;

subjecting both of said first and second semiconductor islands to a first ion doping for introducing a first impurity;

subjecting only said first semiconductor islands to a second ion doping for introducing a second impurity wherein said second impurity has an opposite conductivity type to said first impurity;

directing a pulsed excimer laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed excimer laser beam, thereby irradiating both of said first and second semiconductor islands with said pulsed excimer laser beam.

10. A method according to claim 9 wherein an energy density of said pulsed excimer laser beam is not higher than 300 mJ/cm^2 .

11. A method according to claim 9 wherein said first impurity is phosphorus while said second impurity is boron.

12. A method according to claim 9 wherein each of said first and second semiconductor islands is irradiated with plural pulses of said pulsed excimer laser beam.

13. A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands over a glass substrate;

forming a film comprising silicon oxide over said glass substrate wherein said semiconductor islands are covered by said film;

subjecting said semiconductor islands to an ion doping through said film;

directing a pulsed excimer laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed excimer laser beam, thereby irradiating said semiconductor islands with said pulsed excimer laser beam through said film.

14. A method according to claim 13 wherein an energy density of said pulsed excimer laser beam is not higher than 300 mJ/cm^2 .

15. A method according to claim 13 wherein an impurity selected from the group consisting of phosphorus and boron is selectively introduced into said plurality of semiconductor islands by said ion doping.

16. A method according to claim 13 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed excimer laser beam.

17. A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands comprising silicon and germanium over a substrate;

subjecting said semiconductor islands to an ion doping;

directing a pulsed excimer laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed excimer laser beam, thereby irradiating said semiconductor islands with said pulsed excimer laser beam.

18. A method according to claim 17 wherein an impurity selected from the group consisting of phosphorus and boron is selectively introduced into said plurality of semiconductor islands by said ion doping.

19. A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands comprising silicon and germanium over a substrate;

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forming a film comprising silicon oxide over said glass substrate wherein said semiconductor islands are covered by said film; subjecting said semiconductor islands to an ion doping through said film; directing a pulsed excimer laser beam having a cross section elongated in one direction to said glass substrate; moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed excimer laser beam, thereby irradiating said semiconductor islands with said pulsed excimer laser beam through said film.

20. A method of manufacturing a semiconductor device according to claim 19 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed excimer laser beam.

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